

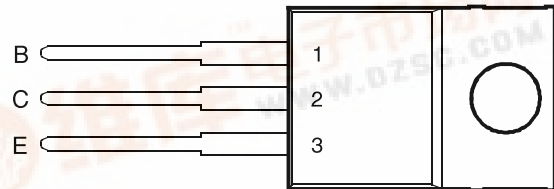
## BULD85KC NPN SILICON TRANSISTOR WITH INTEGRATED DIODE

- **Designed Specifically for High Frequency Electronic Ballasts**
- **Integrated Fast  $t_{rr}$  Anti-Parallel Diode, Enhancing Reliability**
- **Diode  $t_{rr}$  Typically 1  $\mu$ s**
- **Tightly Controlled Transistor Storage Times**
- **Voltage Matched Integrated Transistor and Diode**
- **Characteristics Optimised for Cool Running**
- **Diode-Transistor Charge Coupling Minimised to Enhance Frequency Stability**

### description

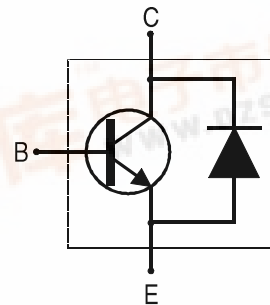
The new BULDxx range of transistors have been designed specifically for use in High Frequency Electronic Ballasts (HFEB's). This range of switching transistors has tightly controlled storage times and an integrated fast  $t_{rr}$  anti-parallel diode. The revolutionary design ensures that the diode has both fast forward and reverse recovery times, achieving the same performance as a discrete anti-parallel diode plus transistor. The integrated diode has minimal charge coupling with the transistor, increasing frequency stability, especially in lower power circuits where the circulating currents are low. By design, this new device offers a voltage matched integrated transistor and anti-parallel diode.

TO-220 PACKAGE  
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

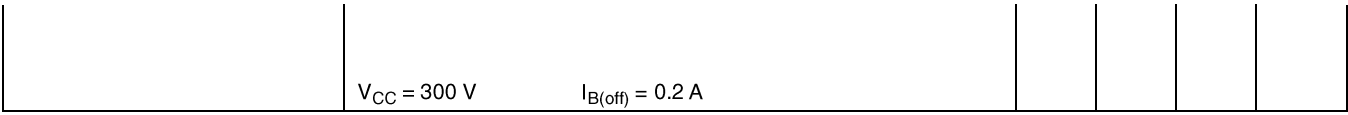
device symbol



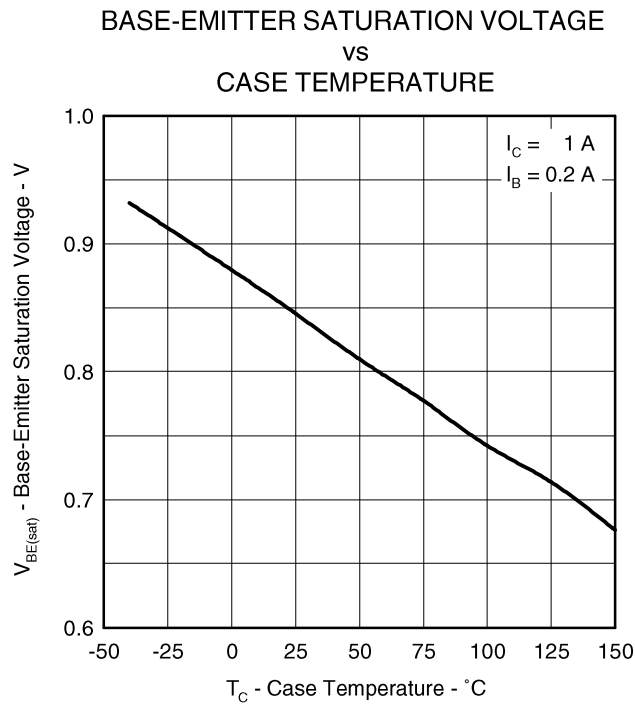
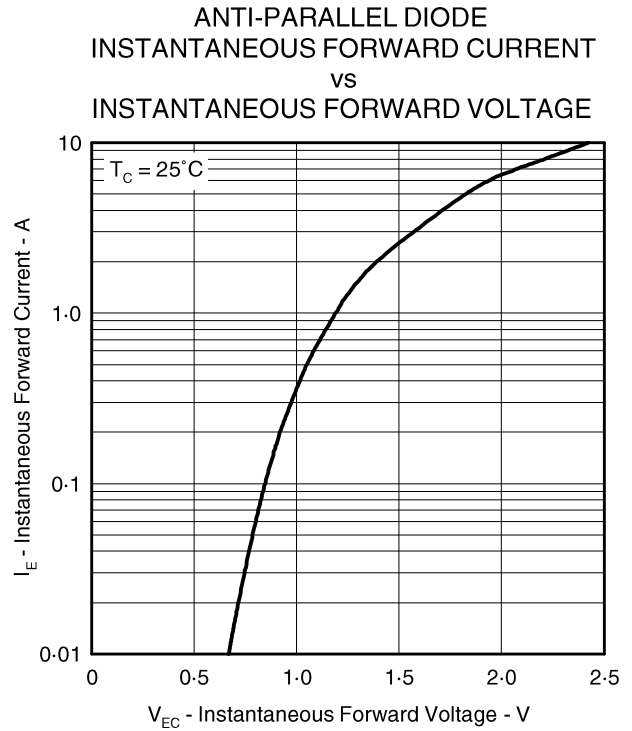
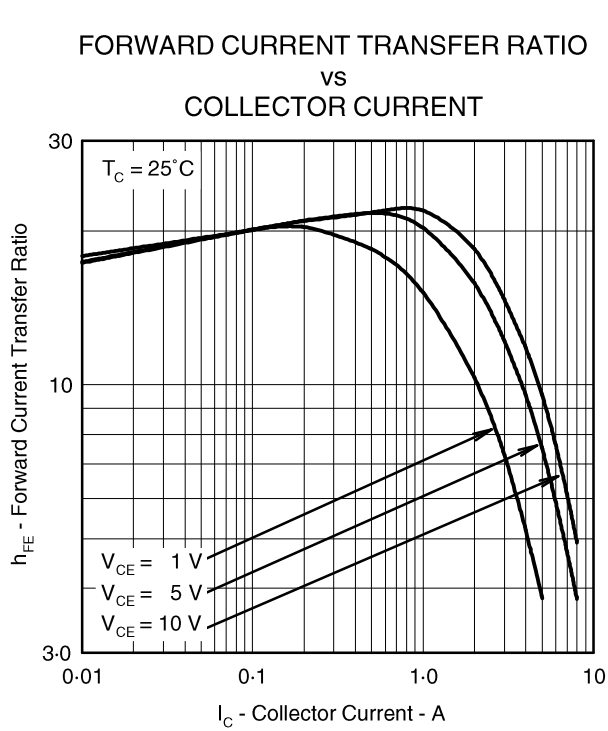
### absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Collector-emitter voltage ( $V_{BE} = 0$ )	$V_{CES}$	600	V
Collector-base voltage ( $I_E = 0$ )	$V_{CBO}$	600	V
Collector-emitter voltage ( $I_B = 0$ )	$V_{CEO}$	400	V
Emitter-base voltage	$V_{EBO}$	9	V
Continuous collector current	$I_C$	6	A
Peak collector current (see Note 1)	$I_{CM}$	8	A
Continuous base current	$I_B$	2	A
Peak base current (see Note 1)	$I_{BM}$	4	A
Continuous device dissipation at (or below) 25°C case temperature	$P_{tot}$	70	W
Maximum average continuous diode forward current at (or below) 25°C case temperature	$I_{E(av)}$	0.5	A
Operating junction temperature range	$T_j$	-65 to +150	°C
Storage temperature range	$T_{stg}$	-65 to +150	°C

NOTE 1: This value applies for  $t_p = 10$  ms, duty cycle  $\leq 2\%$ .



**TYPICAL CHARACTERISTICS**



**BULD85KC**  
**NPN SILICON TRANSISTOR WITH INTEGRATED DIODE**

**MAXIMUM SAFE OPERATING REGIONS**

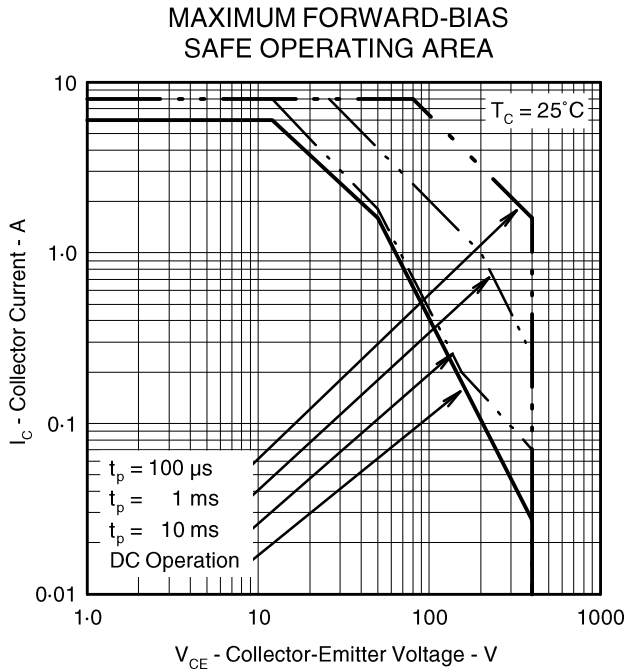


Figure 4.

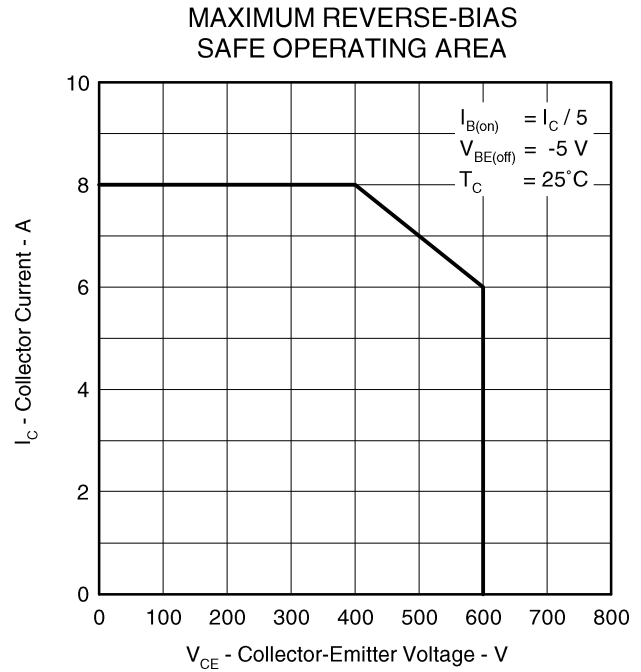


Figure 5.

**THERMAL INFORMATION**

**THERMAL RESPONSE JUNCTION TO AMBIENT  
 vs  
 POWER PULSE DURATION**

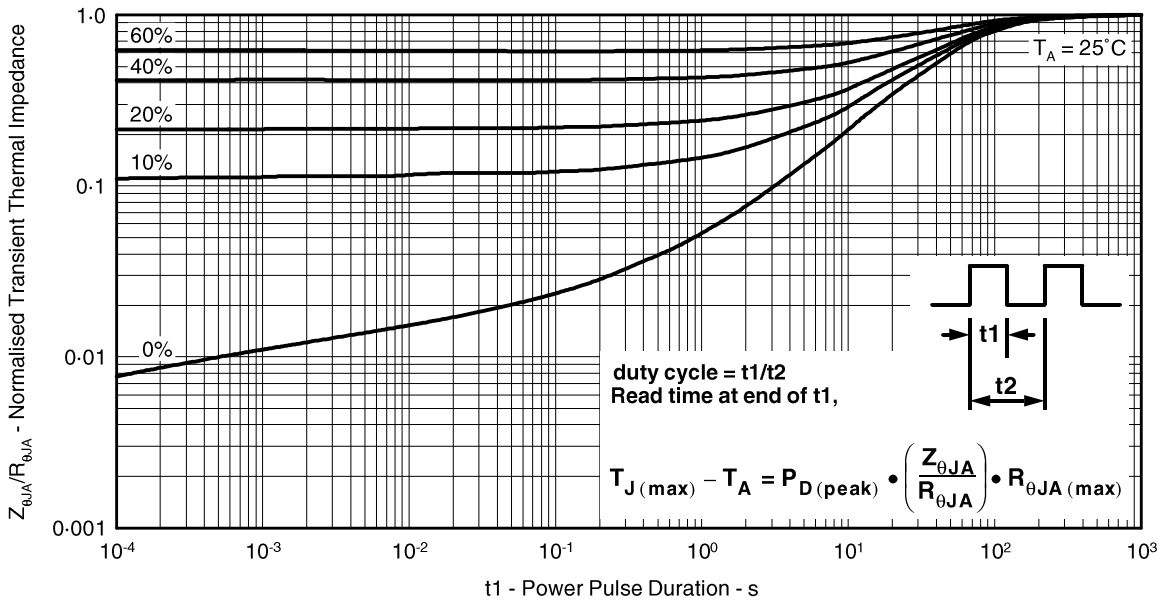


Figure 6.

# BULD85KC

## NPN SILICON TRANSISTOR WITH INTEGRATED DIODE

### THERMAL INFORMATION

THERMAL RESPONSE JUNCTION TO CASE  
VS  
POWER PULSE DURATION

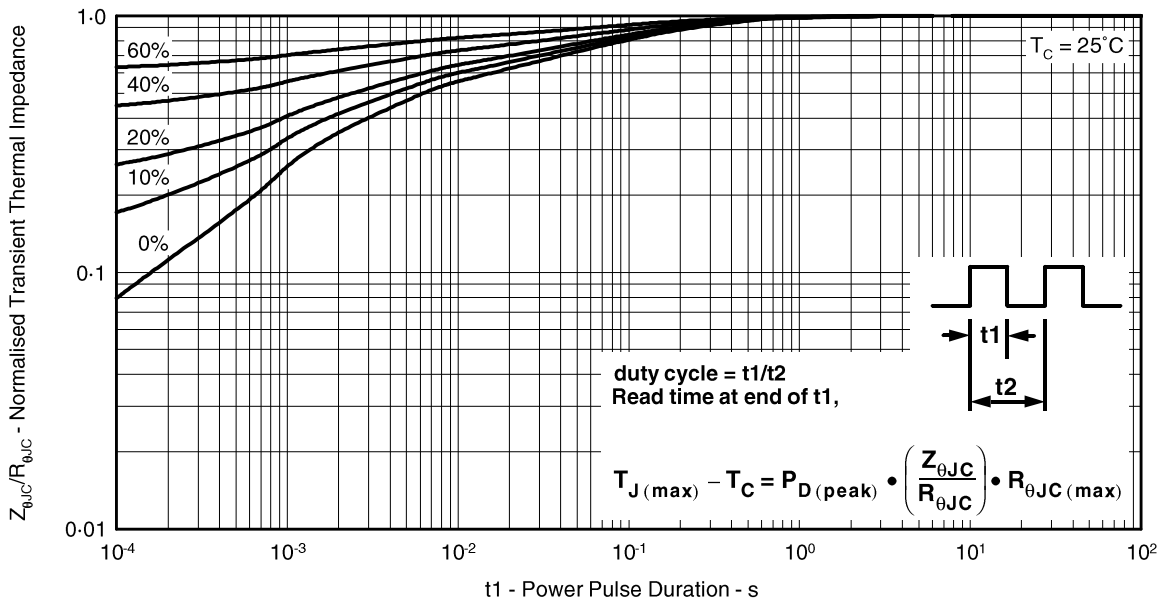


Figure 7.

MAXIMUM POWER DISSIPATION JUNCTION TO AMBIENT  
VS  
POWER PULSE DURATION

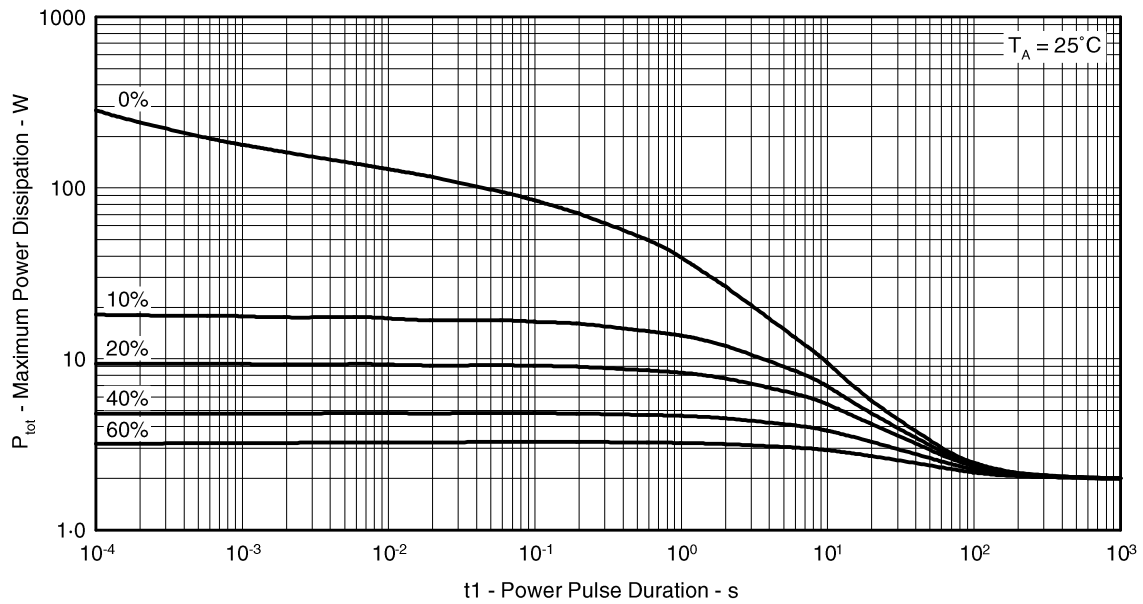
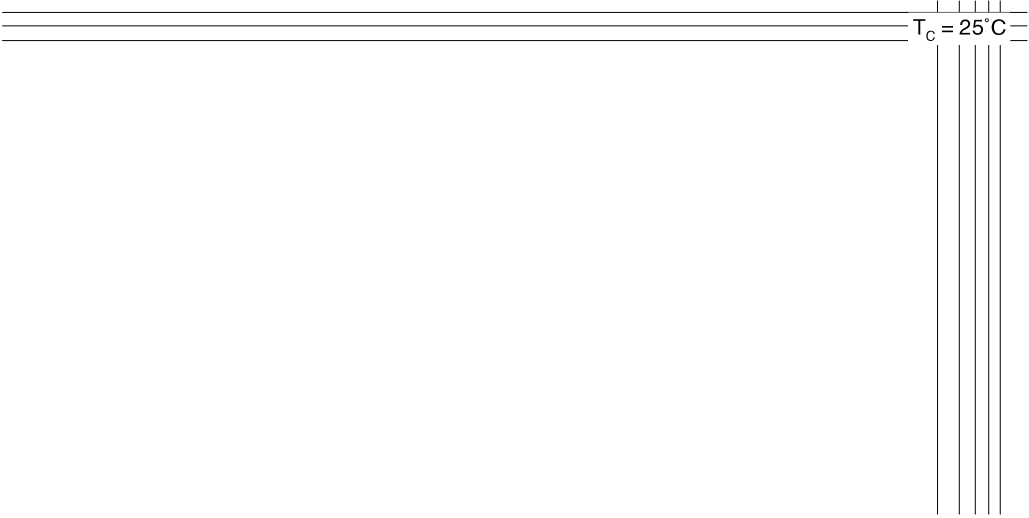


Figure 8.



# BULD85KC

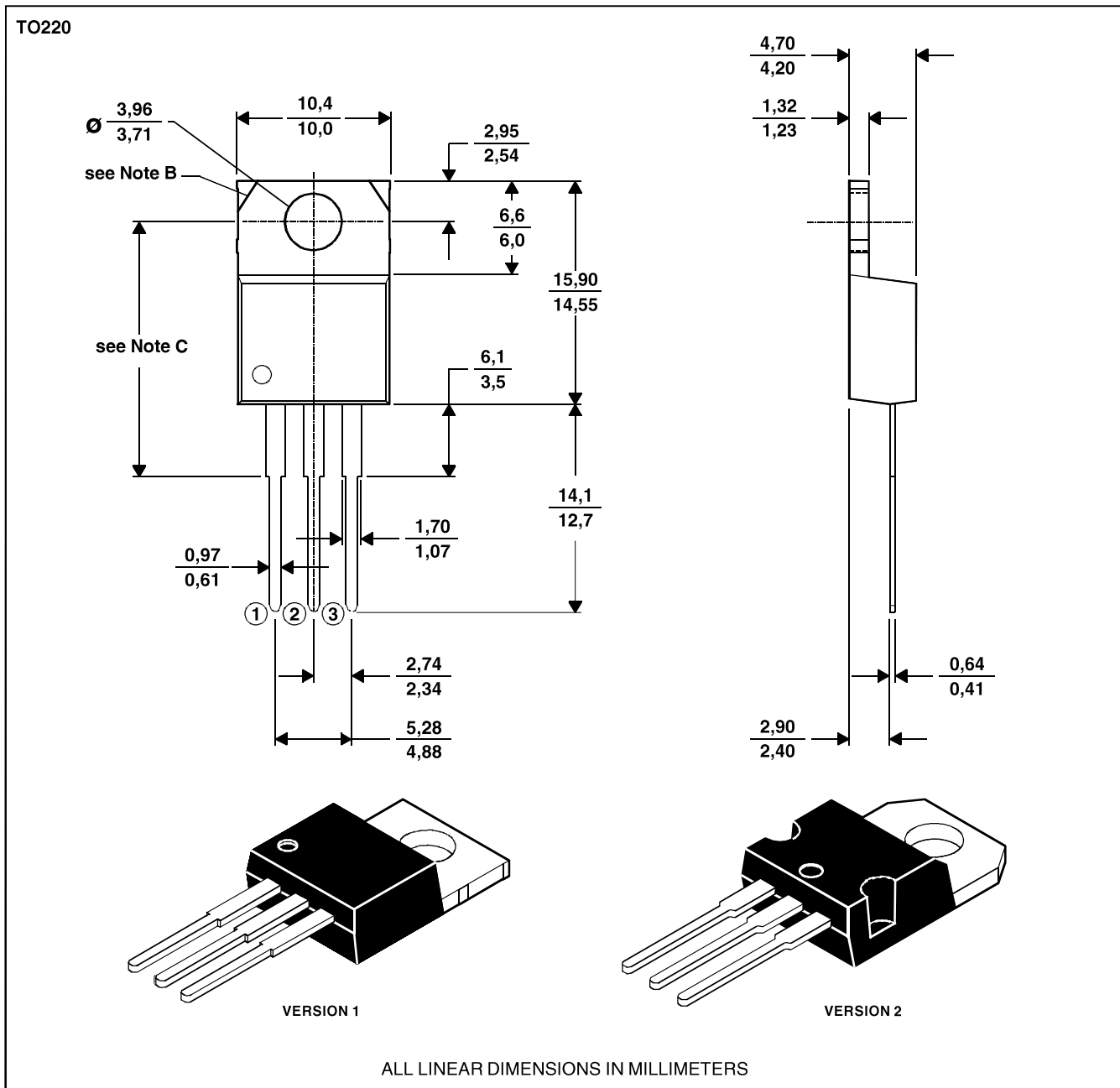
## NPN SILICON TRANSISTOR WITH INTEGRATED DIODE

### MECHANICAL DATA

#### TO-220

#### 3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



- NOTES: A. The centre pin is in electrical contact with the mounting tab.  
 B. Mounting tab corner profile according to package version.  
 C. Typical fixing hole centre stand off height according to package version.  
 Version 1, 18.0 mm. Version 2, 17.6 mm.